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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	3K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFBGA
Supplier Device Package	64-VFBGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100ldabg-u0

RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(2/12)

				(2/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
25 pins	25-pin plastic	Mounted	Α	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0,
25 pins	· · ·	Mounted	7.	R5F1008EALA#U0
	WFLGA (3 \times 3 mm,			R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0,
	0.5 mm pitch)			R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0,
				R5F1008EGLA#U0
				R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0,
				R5F1008EGLA#W0
		Not	Α	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0,
i		mounted		R5F1018EALA#U0
				R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0,
				R5F1018EALA#W0
30 pins	30-pin plastic LSSOP	Mounted	Α	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0,
i	(7.62 mm (300), 0.65			R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0
	mm pitch)			R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0
	min piton)		_	R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0,
				R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0
				R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AGSP#V0, R5F100ACGSP#V0,
			G	R5F100ADGSP#V0, R5F100ACGSF#V0,
				R5F100AFGSP#V0, R5F100AGGSP#V0,
				R5F100AAGSP#X0, R5F100ACGSP#X0,
				R5F100ADGSP#X0,R5F100AEGSP#X0,
				R5F100AFGSP#X0, R5F100AGGSP#X0
		Not	Α	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0,
				R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0
		mounted		R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0,
				R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0,
				R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0
				R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0,
				R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic	Mounted	Α	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0,
	HWQFN (5 × 5 mm,			R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0
	0.5 mm pitch)			R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0,
	0.5 min pitch)			R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0,
				R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0
				R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0,
				R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0,
				R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0
				R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0,
			_	R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not	Α	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0,
		mounted		R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0
				R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0,
			D	R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			٦ ا	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BEDNA#U0
1				R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0,
				R5F101BEDNA#W0, R5F101BCDNA#W0, R5F101BBDNA#W0,
			1	TOT TO TO EDINA#WO, NOT TO TO FOUNA#WO, NOT TO TO EDINA#WO

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



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Table 1-1. List of Ordering Part Numbers

(5/12)

Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
48 pins	48-pin plastic	Mounted	Α	R5F100GAAFB#V0, R5F100GCAFB#V0, R5F100GDAFB#V0,
	LFQFP (7×7 mm,			R5F100GEAFB#V0, R5F100GFAFB#V0, R5F100GGAFB#V0,
	0.5 mm pitch)			R5F100GHAFB#V0, R5F100GJAFB#V0, R5F100GKAFB#V0,
				R5F100GLAFB#V0
				R5F100GAAFB#X0, R5F100GCAFB#X0, R5F100GDAFB#X0,
				R5F100GEAFB#X0, R5F100GFAFB#X0, R5F100GGAFB#X0,
				R5F100GHAFB#X0, R5F100GJAFB#X0, R5F100GKAFB#X0,
				R5F100GLAFB#X0
			D	R5F100GADFB#V0, R5F100GCDFB#V0, R5F100GDDFB#V0,
				R5F100GEDFB#V0, R5F100GFDFB#V0, R5F100GGDFB#V0,
				R5F100GHDFB#V0, R5F100GJDFB#V0, R5F100GKDFB#V0,
				R5F100GLDFB#V0
				R5F100GADFB#X0, R5F100GCDFB#X0, R5F100GDDFB#X0,
				R5F100GEDFB#X0, R5F100GFDFB#X0, R5F100GGDFB#X0,
				R5F100GHDFB#X0, R5F100GJDFB#X0, R5F100GKDFB#X0,
				R5F100GLDFB#X0
			G	R5F100GAGFB#V0, R5F100GCGFB#V0, R5F100GDGFB#V0,
				R5F100GEGFB#V0, R5F100GFGFB#V0, R5F100GGGFB#V0,
				R5F100GHGFB#V0, R5F100GJGFB#V0
				R5F100GAGFB#X0, R5F100GCGFB#X0, R5F100GDGFB#X0,
				R5F100GEGFB#X0, R5F100GFGFB#X0, R5F100GGGFB#X0,
				R5F100GHGFB#X0, R5F100GJGFB#X0
		Not	Α	R5F101GAAFB#V0, R5F101GCAFB#V0, R5F101GDAFB#V0,
		mounted		R5F101GEAFB#V0, R5F101GFAFB#V0, R5F101GGAFB#V0,
				R5F101GHAFB#V0, R5F101GJAFB#V0, R5F101GKAFB#V0,
				R5F101GLAFB#V0
				R5F101GAAFB#X0, R5F101GCAFB#X0, R5F101GDAFB#X0,
				R5F101GEAFB#X0, R5F101GFAFB#X0, R5F101GGAFB#X0,
				R5F101GHAFB#X0, R5F101GJAFB#X0, R5F101GKAFB#X0,
				R5F101GLAFB#X0
			D	R5F101GADFB#V0, R5F101GCDFB#V0, R5F101GDDFB#V0,
				R5F101GEDFB#V0, R5F101GFDFB#V0, R5F101GGDFB#V0,
				R5F101GHDFB#V0, R5F101GJDFB#V0, R5F101GKDFB#V0,
				R5F101GLDFB#V0
				R5F101GADFB#X0, R5F101GCDFB#X0, R5F101GDDFB#X0,
				R5F101GEDFB#X0, R5F101GFDFB#X0, R5F101GGDFB#X0,
1				R5F101GHDFB#X0, R5F101GJDFB#X0, R5F101GKDFB#X0,
				R5F101GLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(10/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	Mounted	А	R5F100MFAFA#V0, R5F100MGAFA#V0, R5F100MHAFA#V0, R5F100MJAFA#V0, R5F100MKAFA#V0, R5F100MLAFA#V0 R5F100MFAFA#X0, R5F100MGAFA#X0, R5F100MHAFA#X0, R5F100MJAFA#X0, R5F100MKAFA#X0, R5F100MLAFA#X0
			D	R5F100MFDFA#V0, R5F100MGDFA#V0, R5F100MHDFA#V0, R5F100MJDFA#V0, R5F100MKDFA#V0, R5F100MFDFA#X0, R5F100MFDFA#X0, R5F100MFDFA#X0, R5F100MJDFA#X0, R5F100MKDFA#X0, R5F100MLDFA#X0
			G	R5F100MFGFA#V0, R5F100MGGFA#V0, R5F100MHGFA#V0, R5F100MJGFA#V0 R5F100MFGFA#X0, R5F100MGGFA#X0, R5F100MJGFA#X0, R5F100MJGFA#X0
		Not mounted	A	R5F101MFAFA#V0, R5F101MGAFA#V0, R5F101MHAFA#V0, R5F101MJAFA#V0, R5F101MKAFA#V0, R5F101MLAFA#V0 R5F101MFAFA#X0, R5F101MGAFA#X0, R5F101MJAFA#X0, R5F101MKAFA#X0, R5F101MLAFA#X0
			D	R5F101MFDFA#V0, R5F101MGDFA#V0, R5F101MHDFA#V0, R5F101MJDFA#V0, R5F101MKDFA#V0, R5F101MLDFA#V0 R5F101MFDFA#X0, R5F101MGDFA#X0, R5F101MHDFA#X0, R5F101MJDFA#X0, R5F101MKDFA#X0, R5F101MJDFA#X0
	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	Mounted	A	R5F100MFAFB#V0, R5F100MGAFB#V0, R5F100MHAFB#V0, R5F100MJAFB#V0, R5F100MKAFB#V0, R5F100MLAFB#V0 R5F100MFAFB#X0, R5F100MGAFB#X0, R5F100MJAFB#X0, R5F100MKAFB#X0, R5F100MLAFB#X0
			D	R5F100MFDFB#V0, R5F100MGDFB#V0, R5F100MHDFB#V0, R5F100MJDFB#V0, R5F100MKDFB#V0, R5F100MLDFB#V0 R5F100MFDFB#X0, R5F100MGDFB#X0, R5F100MHDFB#X0, R5F100MJDFB#X0, R5F100MKDFB#X0, R5F100MLDFB#X0
			G	R5F100MFGFB#V0, R5F100MGGFB#V0, R5F100MHGFB#V0, R5F100MJGFB#V0 R5F100MFGFB#X0, R5F100MGGFB#X0, R5F100MJGFB#X0, R5F100MJGFB#X0
		Not mounted	А	R5F101MFAFB#V0, R5F101MGAFB#V0, R5F101MHAFB#V0, R5F101MJAFB#V0, R5F101MKAFB#V0, R5F101MFAFB#X0, R5F101MGAFB#X0, R5F101MHAFB#X0, R5F101MJAFB#X0, R5F101MKAFB#X0, R5F101MLAFB#X0
			D	R5F101MFDFB#V0, R5F101MGDFB#V0, R5F101MHDFB#V0, R5F101MJDFB#V0, R5F101MKDFB#V0, R5F101MLDFB#V0 R5F101MFDFB#X0, R5F101MGDFB#X0, R5F101MHDFB#X0, R5F101MJDFB#X0, R5F101MKDFB#X0, R5F101MLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



RL78/G13 1. OUTLINE

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

												(1/2)
	Item	20-	pin	24-	pin	25	-pin	30-	pin	32-	pin	36-	pin
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash me	emory (KB)	16 to	o 64	16 t	o 64	16 t	o 64	16 to	128	16 to	128	16 to	128
Data flash me	mory (KB)	4	_	4	-	4	=	4 to 8	=	4 to 8	-	4 to 8	=
RAM (KB)		2 to	4 ^{Note1}	2 to	4 ^{Note1}	2 to	4 ^{Note1}	2 to 1	2 ^{Note1}	2 to ⁻	12 ^{Note1}	2 to 1	2 ^{Note1}
Address space	е	1 MB											
Main system clock	High-speed system clock	HS (Hig HS (Hig LS (Lov	jh-speed jh-speed v-speed	I main) m I main) m main) m	node: 1 t node: 1 t ode: 1 tc	o 20 MH o 16 MH o 8 MHz	z (V _{DD} = z (V _{DD} =	tem cloc 2.7 to 5. 2.4 to 5. 8 to 5.5 1.6 to 5.5	5 V), 5 V), V),	(EXCLK)			
	High-speed on-chip oscillator	HS (Hig LS (Lov	jh-speed v-speed	l main) m main) m	node: 1 t ode: 1 t	:o 16 MH :o 8 MHz	Iz (Vdd =	2.7 to 5. 2.4 to 5. 1.8 to 5.5 1.6 to 5.5	5 V), V),				
Subsystem clo	ock						-	-					
Low-speed on	n-chip oscillator	15 kHz	(TYP.)										
General-purpo	ose registers	(8-bit re	gister ×	8) × 4 ba	nks								
Minimum instr	ruction execution time	0.03125	5 μs (Hig	h-speed	on-chip	oscillato	r: fін = 3	2 MHz op	peration)			
		0.05 μ s (High-speed system clock: f _{MX} = 20 MHz operation)											
Instruction set	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 											
I/O port	Total	1	6	2	0	2	21	2	6	2	8	3	2
	CMOS I/O	1 (N-ch C [Vpp wit voltag	D.D. I/O thstand	(N-ch C	5 D.D. I/O thstand ge]: 6)	(N-ch (5 D.D. I/O thstand ge]: 6)	2 (N-ch C [V _{DD} wit voltag	D.D. I/O thstand	2 (N-ch ([V _{DD} wi voltag	thstand	(N-ch C [V _{DD} with voltage	thstand
	CMOS input	3	3	;	3	;	3	3	3	;	3	3	3
	CMOS output	-	-	-	-		1	_	-	-	-	-	-
	N-ch O.D. I/O (withstand voltage: 6 V)	=	_	2	2	:	2	2	2	(3	3	3
Timer	16-bit timer						8 cha	nnels					
	Watchdog timer						1 cha	annel					
	Real-time clock (RTC)						1 chan	nel Note 2					
	12-bit interval timer (IT)						1 cha	annel					
	Timer output	3 chann (PWM c 2 Note 3)		4 chanr (PWM	nels outputs:	3 Note 3)				M output M output			
	RTC output						=	=					
· · · · · · · · · · · · · · · · · · ·													

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (fill) is selected

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit	
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA	
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA	
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA	
	І ОН2	Per pin	P20 to P27, P150 to P156	-0.5	mA	
		Total of all pins		-2	mA	
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA	
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA	
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA	
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA	
		Total of all pins		5	mA	
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C	
temperature	In flash memory programming mode					
Storage temperature	Tstg			-65 to +150	°C	

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.54	1.63	mA
current	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.54	1.63	mA
				$f_{IH} = 24 \text{ MHz}^{\text{Note 4}}$	V _{DD} = 5.0 V		0.44	1.28	mA
					V _{DD} = 3.0 V		0.44	1.28	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.00	mA
					V _{DD} = 3.0 V		0.40	1.00	mA
			LS (low-	fih = 8 MHz Note 4	V _{DD} = 3.0 V		260	530	μА
			speed main) mode Note 7		V _{DD} = 2.0 V		260	530	μА
			LV (low-	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA
		r	voltage main) mode		V _{DD} = 2.0 V		420	640	μА
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	1.17	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
				V _{DD} = 3.0 V	Resonator connection		0.45	1.17	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 5.0 \text{ V}$	Resonator connection		0.26	0.67	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 3.0 \text{ V}$	Resonator connection		0.26	0.67	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μΑ
			speed main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		145	380	μΑ
			mode	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μΑ
				$V_{DD} = 2.0 \text{ V}$	Resonator connection		145	380	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μΑ
			clock	T _A = -40°C	Resonator connection		0.44	0.76	μΑ
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μΑ
				T _A = +25°C	Resonator connection		0.49	0.76	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.37	1.17	μΑ
				T _A = +50°C	Resonator connection		0.56	1.36	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.53	1.97	μΑ
				T _A = +70°C	Resonator connection		0.72	2.16	μA
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.82	3.37	μΑ
				T _A = +85°C	Resonator connection		1.01	3.56	μΑ
	IDD3 ^{Note 6} STOP T _A = -40°C				0.18	0.50	μΑ		
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μΑ
			T _A = +50°C				0.30	1.10	μΑ
			T _A = +70°C				0.46	1.90	μА
			T _A = +85°C				0.75	3.30	μΑ

(Notes and Remarks are listed on the next page.)



(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	DD2 Note 2	HALT	HS (high-	fin = 32 MHz Note 4	V _{DD} = 5.0 V		0.62	1.86	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	1.86	mA
			mode	fih = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	1.45	mA
					V _{DD} = 3.0 V		0.50	1.45	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.11	mA
					V _{DD} = 3.0 V		0.44	1.11	mA
			LS (low-	fin = 8 MHz Note 4	V _{DD} = 3.0 V		290	620	μA
			speed main) mode Note 7		V _{DD} = 2.0 V		290	620	μΑ
			LV (low-	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		440	680	μΑ
			voltage main) mode		VDD = 2.0 V		440	680	μΑ
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.08	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	1.28	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	1.08	mA
			V _{DD} = 3.0 V	Resonator connection		0.48	1.28	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.63	mA
			V _{DD} = 5.0 V	Resonator connection		0.28	0.71	mA	
				f _M x = 10 MHz ^{Note 3} ,	Square wave input		0.21	0.63	mA
				V _{DD} = 3.0 V	Resonator connection		0.28	0.71	mA
			LS (low- speed main) mode Note 7	f _M x = 8 MHz ^{Note 3} ,	Square wave input		110	360	μА
				V _{DD} = 3.0 V	Resonator connection		160	420	μΑ
				fmx = 8 MHz ^{Note 3} ,	Square wave input		110	360	μΑ
				V _{DD} = 2.0 V	Resonator connection		160	420	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.47	0.80	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μΑ
				T _A = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μΑ
				T _A = +50°C	Resonator connection		0.60	2.49	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μΑ
				T _A = +70°C	Resonator connection		0.83	4.22	μА
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.09	8.04	μΑ
			T _A = +85°C	Resonator connection		1.28	8.23	μА	
	IDD3 ^{Note 6}	STOP	T _A = -40°C				0.19	0.52	μΑ
		mode ^{Note 8}	T _A = +25°C				0.25	0.52	μΑ
			T _A = +50°C				0.32	2.21	μΑ
			T _A = +70°C				0.55	3.94	μΑ
			T _A = +85°C				1.00	7.95	μA

(Notes and Remarks are listed on the next page.)



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions		speed	high- I main) ode		/-speed Mode	voltage	low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate folk Note 4		5.3		1.3		0.6	Mbps
			$1.8 \ V \le EV_{DD0} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V$			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with EVDD0≥Vb.
- 3. The following conditions are required for low voltage interface when $E_{VDDO} < V_{DD}$.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq V_{DD} \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq V_{DD} \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. $V_b[V]$: Communication line voltage

- 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmcκ: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed Mode	`	/-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸı	$\begin{array}{l} 4.0~V \leq EV_{DD0} \leq 5.5~V, \\ 2.7~V \leq V_b \leq 4.0~V, \end{array}$	81		479		479		ns
		$C_b = 30$ pF, $R_b = 1.4$ k Ω							
			177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$ \begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array} $	479		479		479		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
SIp hold time (from SCKp↑) Note 1	t KSI1	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							
Delay time from SCKp↓ to	tkso1	$ \begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \end{array} $		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, $		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{c} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω							

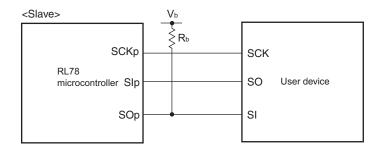
Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

CSI mode connection diagram (during communication at different potential)



- Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condit	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$		1.2	±5.0	LSB
		EVDD0 = AV _{REFP} = V _{DD} Notes 3, 4	$\begin{array}{ c c c }\hline 1.6 \ V \leq AV_{REFP} \leq 5.5 \ V^{Note} \\ & & \\ &$		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI26	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±3.5	LSB
1		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±6.0	LSB
Differential linearity	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
error ^{Note 1}		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI26	,	0		AVREFP and EVDD0	٧

- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

- **4.** When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins -170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	- 70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	Та	In normal operati	on mode programming mode	-40 to +105	°C
	l				

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions			ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$	$0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$		Note 1	bps
			$V,$ $2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.6 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			Note 3	bps
			$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps
			2.4 V ≤ EV _{DD0} < 3.3			Note 5	bps
	$V,$ $1.6~V \le V_b \le 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 V$		0.43 Note 6	Mbps		

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (h	HS (high-speed main) Mode			Unit
				ndard ode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	-	_	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	-	-	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	t BUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

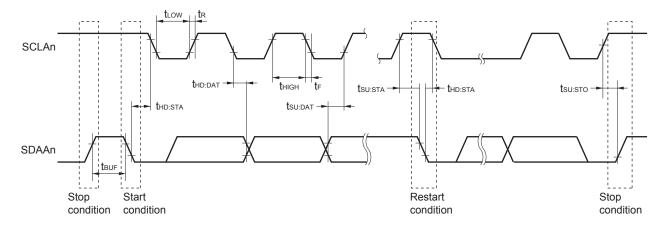
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

<R>

3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

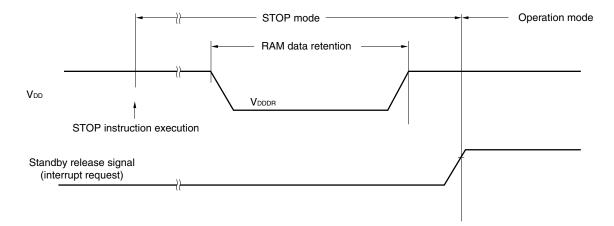
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V _{DDDR}		1.44 ^{Note}		5.5	٧

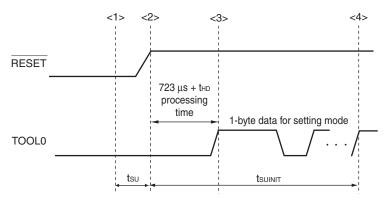
Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

 t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.10 52-pin Products

R5F100JCAFA, R5F100JDAFA, R5F100JEAFA, R5F100JFAFA, R5F100JGAFA, R5F100JHAFA, R5F100JJAFA, R5F100JKAFA, R5F100JLAFA

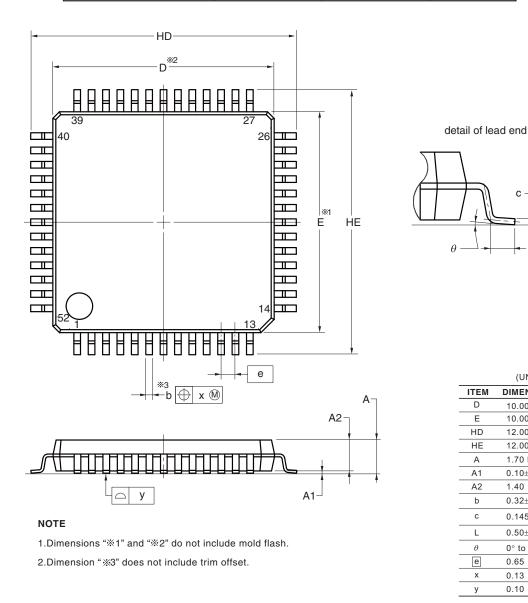
R5F101JCAFA, R5F101JDAFA, R5F101JEAFA, R5F101JFAFA, R5F101JGAFA, R5F101JJAFA, R5F101JJAFA, R5F101JAFA, R5F101JKAFA, R5F101JLAFA

R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JDFA, R5F100JPA, R R5F100JKDFA, R5F100JLDFA

R5F101JCDFA, R5F101JDDFA, R5F101JEDFA, R5F101JFDFA, R5F101JDFA, R5 R5F101JKDFA, R5F101JLDFA

R5F100JCGFA, R5F100JDGFA, R5F100JEGFA, R5F100JFGFA, R5F100JGGFA, R5F100JHGFA, R5F100JJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]	
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3	



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(UNIT:mm)

DIMENSIONS

10.00±0.10

10.00±0.10

12.00±0.20

12.00±0.20 1.70 MAX.

 0.10 ± 0.05 1.40

0.32±0.05

 $0.50 {\pm} 0.15$

 0° to 8° 0.65

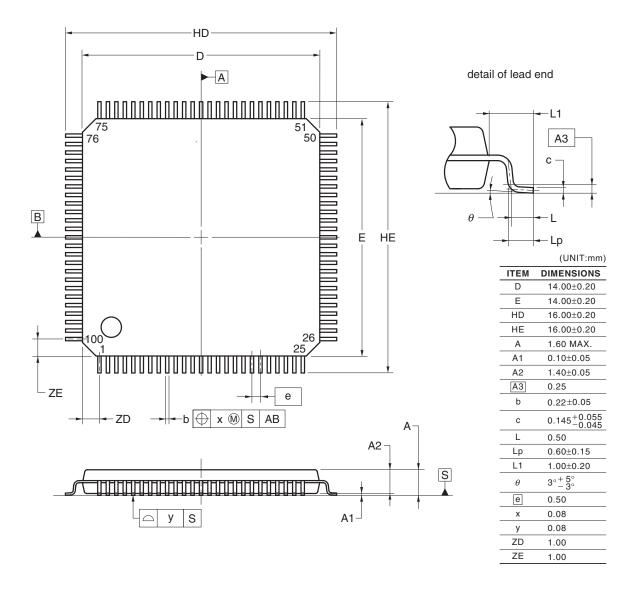
0.13 0.10

0.145±0.055

4.13 100-pin Products

R5F100PFAFB, R5F100PGAFB, R5F100PHAFB, R5F100PJAFB, R5F100PKAFB, R5F100PLAFB R5F101PFAFB, R5F101PGAFB, R5F101PHAFB, R5F101PJAFB, R5F101PKAFB, R5F101PLAFB R5F100PFDFB, R5F100PGDFB, R5F100PHDFB, R5F100PJDFB, R5F100PKDFB, R5F101PGDFB, R5F101PGDFB, R5F101PJDFB, R5F101PJDFB, R5F101PLDFB R5F100PFGFB, R5F100PGGFB, R5F100PHGFB, R5F100PJGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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RL78/G13 Data Sheet

			Description		
Rev.	Date	Page	Summary		
1.00	Feb 29, 2012	-	First Edition issued		
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count		
			corrected.		
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.		
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.		
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.		
		59, 63, 67	Descriptions of Note 8 in a table corrected.		
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.		
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.		
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.		
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.		
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.		
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.		
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.		
3.00	Aug 02, 2013	1	Modification of 1.1 Features		
		3	Modification of 1.2 List of Part Numbers		
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution		
		16 to 32	Modification of package type in 1.3.1 to 1.3.14		
		33	Modification of description in 1.4 Pin Identification		
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions		
		55	Modification of description in table of Absolute Maximum Ratings (T _A = 25°C)		
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics		
		57	Modification of table in 2.2.2 On-chip oscillator characteristics		
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics		
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics		
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-		
		68	pin products Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-		
		70	pin products Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to		
		72	100-pin products Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-		
			pin products		
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products		
		75	Modification of (4) Peripheral Functions (Common to all products)		
		77	Modification of table in 2.4 AC Characteristics		
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation		
		80	Modification of figures of AC Timing Test Points and External System Clock Timing		

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